

HIGH FREQUENCY LOW NOISE AMPLIFIER
NPN SILICON EPITAXIAL TRANSISTOR

DESCRIPTION

The 2SC3355 is an NPN silicon epitaxial transistor designed for low noise amplifier at VHF, UHF and CATV band.

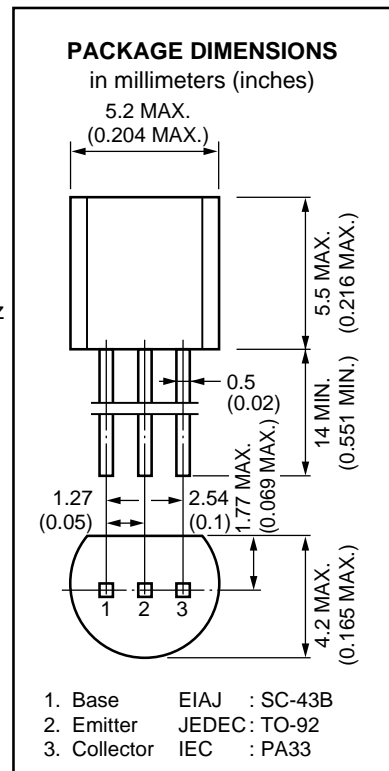
It has large dynamic range and good current characteristic.

FEATURES

- Low Noise and High Gain
 NF = 1.1 dB TYP., $G_a = 8.0$ dB TYP. @ $V_{CE} = 10$ V, $I_c = 7$ mA, $f = 1.0$ GHz
 NF = 1.1 dB TYP., $G_a = 9.0$ dB TYP. @ $V_{CE} = 10$ V, $I_c = 40$ mA, $f = 1.0$ GHz
- High Power Gain
 MAG = 11 dB TYP. @ $V_{CE} = 10$ V, $I_c = 20$ mA, $f = 1.0$ GHz

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C)

Collector to Base Voltage	V_{CB0}	20	V
Collector to Emitter Voltage	V_{CEO}	12	V
Emitter to Base Voltage	V_{EBO}	3.0	V
Collector Current	I_c	100	mA
Total Power Dissipation	P_T	600	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-65 to +150	°C



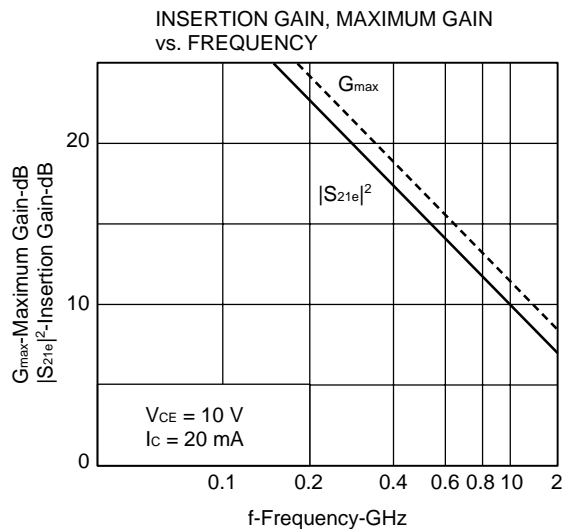
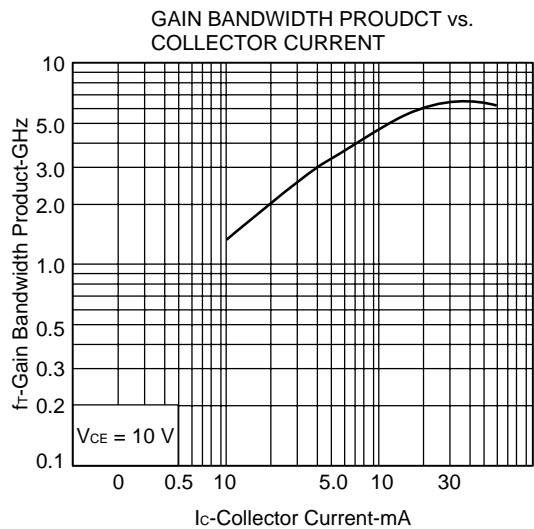
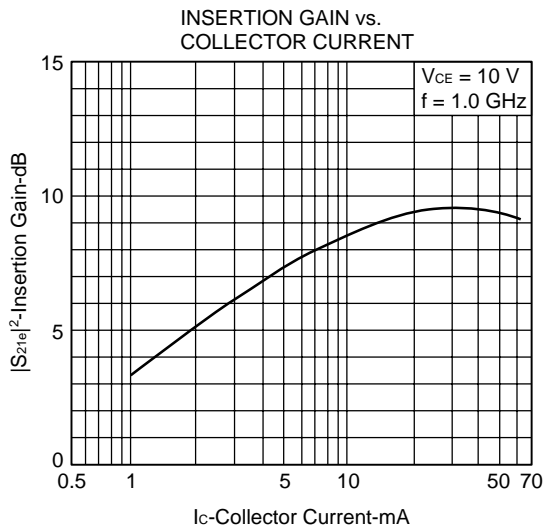
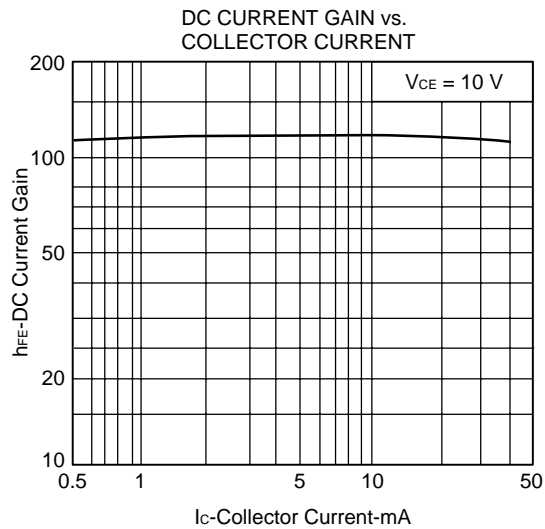
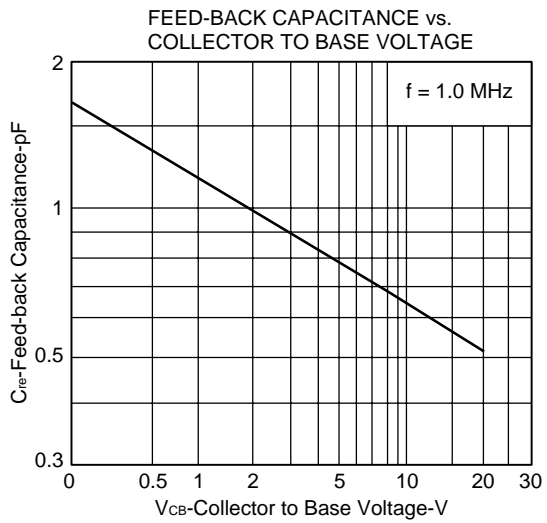
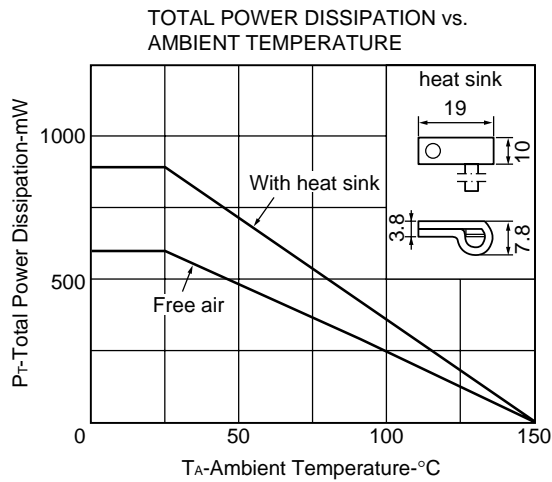
ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C)

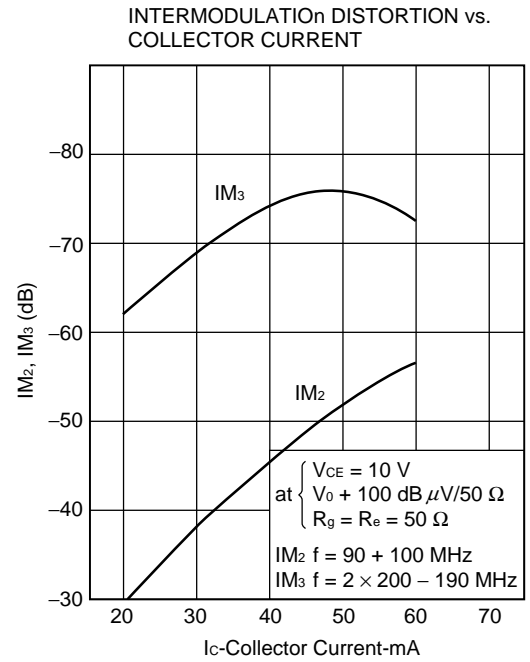
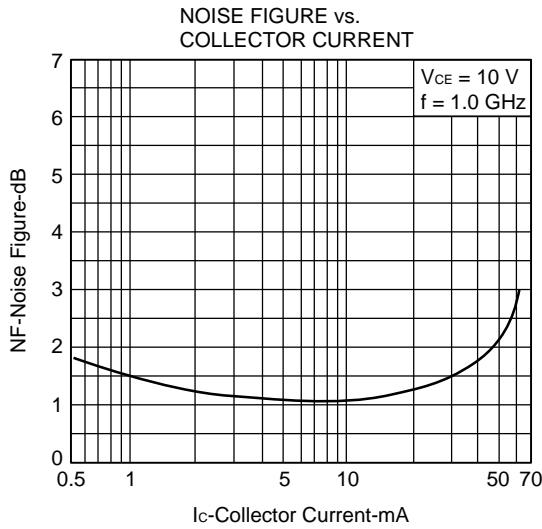
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I_{CBO}			1.0	μ A	$V_{CB} = 10$ V, $I_E = 0$
Emitter Cutoff Current	I_{EBO}			1.0	μ A	$V_{EB} = 1.0$ V, $I_c = 0$
DC Current Gain	h_{FE}	50	120	300		$V_{CE} = 10$ V, $I_c = 20$ mA
Gain Bandwidth Product	f_T		6.5		GHz	$V_{CE} = 10$ V, $I_c = 20$ mA
Output Capacitance	C_{ob}		0.65	1.0	pF	$V_{CB} = 10$ V, $I_E = 0$, $f = 1.0$ MHz
Insertion Power Gain	$ S_{21e} ^2$		9.5		dB	$V_{CE} = 10$ V, $I_c = 20$ mA, $f = 1.0$ GHz
Noise Figure	NF		1.1		dB	$V_{CE} = 10$ V, $I_c = 7$ mA, $f = 1.0$ GHz
Noise Figure	NF		1.8	3.0	dB	$V_{CE} = 10$ V, $I_c = 40$ mA, $f = 1.0$ GHz

hFE Classification

Class	K
Marking	K
h_{FE}	50 to 300

TYPICAL CHARACTERISTICS (T_A = 25 °C)





S-PARAMETER

$V_{CE} = 10\text{ V}, I_c = 20\text{ mA}, Z_o = 50\ \Omega$

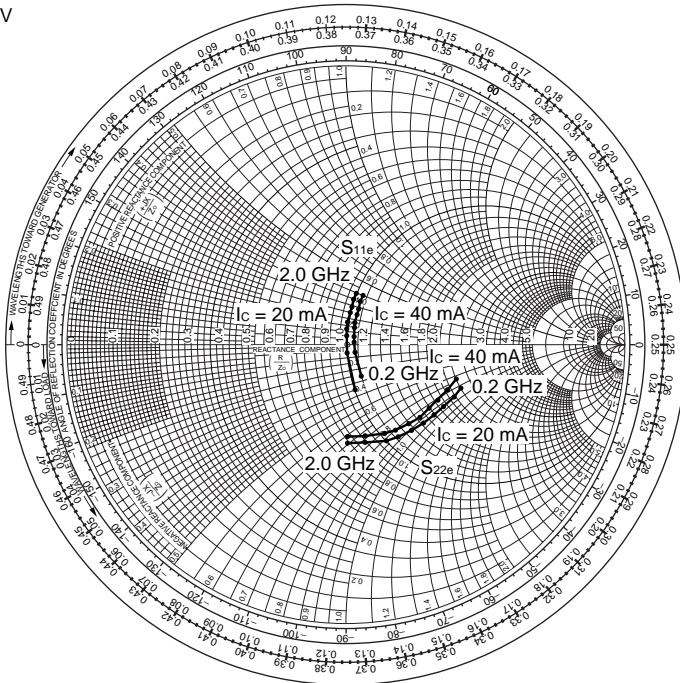
f (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
200	0.173	-80.3	13.652	103.4	0.041	73.8	0.453	-21.8
400	0.054	-77.0	7.217	85.1	0.066	71.2	0.427	-26.0
600	0.013	-57.9	4.936	74.0	0.113	69.3	0.428	-30.8
800	0.028	81.8	3.761	62.3	0.144	67.0	0.414	-37.2
1000	0.062	82.2	3.094	58.3	0.183	64.7	0.392	-43.2
1200	0.091	80.7	2.728	52.9	0.215	61.7	0.377	-51.4
1400	0.121	80.2	2.321	44.9	0.240	58.7	0.359	-58.3
1600	0.148	80.1	2.183	36.4	0.288	50.7	0.354	-67.2
1800	0.171	80.0	1.892	30.2	0.305	46.8	0.345	-80.0
2000	0.207	79.9	1.814	21.4	0.344	39.1	0.344	-90.4

$V_{CE} = 10\text{ V}, I_c = 40\text{ mA}, Z_o = 50\ \Omega$

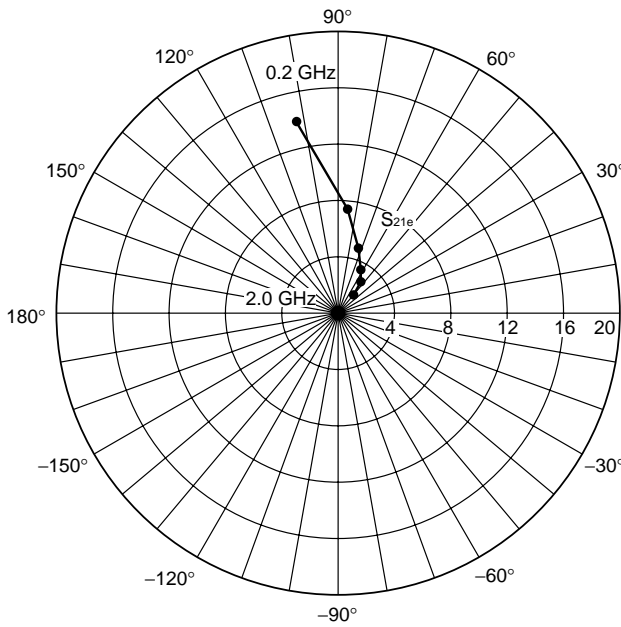
f (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
200	0.011	-60.1	13.76	105.4	0.040	-73.3	0.421	-17.5
400	0.028	-42.9	7.338	82.9	0.069	66.7	0.416	-22.8
600	0.027	25.1	4.996	72.7	0.114	69.4	0.414	-28.7
800	0.043	65.7	3.801	61.9	0.144	67.8	0.406	-35.7
1000	0.074	75.1	3.134	57.6	0.183	63.4	0.386	-41.8
1200	0.098	75.6	2.759	52.4	0.221	62.1	0.373	-49.8
1400	0.120	74.1	2.351	44.4	0.247	55.7	0.356	-56.3
1600	0.146	75.8	2.203	36.0	0.291	49.6	0.347	-66.6
1800	0.171	77.2	1.910	29.9	0.299	46.0	0.342	-78.8
2000	0.205	78.0	1.825	21.3	0.344	39.4	0.335	-89.6

S-PARAMETER

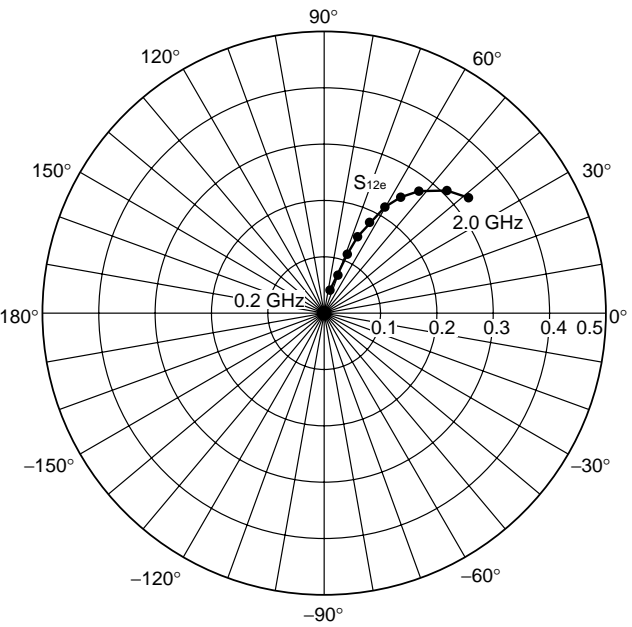
S_{11e}, S_{22e}-FREQUENCY CONDITION V_{CE} = 10 V



S_{21e}-FREQUENCY CONDITION V_{CE} = 10 V
I_c = 40 mA



S_{12e}-FREQUENCY CONDITION V_{CE} = 10 V
I_c = 40 mA



[MEMO]

[MEMO]

[MEMO]

No part of this document may be copied or reproduced in any form or by any means without the prior written consent of NEC Corporation. NEC Corporation assumes no responsibility for any errors which may appear in this document.

NEC Corporation does not assume any liability for infringement of patents, copyrights or other intellectual property rights of third parties by or arising from use of a device described herein or any other liability arising from use of such device. No license, either express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of NEC Corporation or others.

While NEC Corporation has been making continuous effort to enhance the reliability of its semiconductor devices, the possibility of defects cannot be eliminated entirely. To minimize risks of damage or injury to persons or property arising from a defect in an NEC semiconductor device, customers must incorporate sufficient safety measures in its design, such as redundancy, fire-containment, and anti-failure features.

NEC devices are classified into the following three quality grades:

"Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.

Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices is "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact an NEC sales representative in advance.

Anti-radioactive design is not implemented in this product.